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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/711,624	09/29/2004	Chiu-Tsung Huang	9919-US-PA-1	5623	
31561 75	31561 7590 02/23/2005			EXAMINER	
	JN INTELLECTUAL F	TRA, ANH QUAN			
7 FLOOR-1, NO. 100 ROOSEVELT ROAD, SECTION 2 TAIPEI, 100					
			ART UNIT	PAPER NUMBER	
			2816		
TAIWAN			DATE MAILED: 02/23/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)				
Office Action Summers	10/711,624	HUANG ET AL.				
Office Action Summary	Examiner	Art Unit				
	Quan Tra	2816				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).						
Status						
1) Responsive to communication(s) filed on 29 Se	eptember 2004.	•				
<u> </u>	☐ This action is FINAL . 2b)☑ This action is non-final.					
3) Since this application is in condition for allowan						
closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 45	3 O.G. 213.				
Disposition of Claims						
4) Claim(s) 1 is/are pending in the application.						
4a) Of the above claim(s) is/are withdraw	4a) Of the above claim(s) is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.		•				
6)⊠ Claim(s) <u>1</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/or	election requirement.	•				
Application Papers						
9)☐ The specification is objected to by the Examine	Norma en afo					
10) The drawing(s) filed on is/are: a) □ acce	epted or b) objected to by the E	Examiner.				
Applicant may not request that any objection to the						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11) The oath or declaration is objected to by the Ex	aminer. Note the attached Office	Action or form PTO-152.				
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some col None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.						
Attachment(s)						
1) Notice of References Cited (PTO-892)	4) Interview Summary					
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	Paper No(s)/Mail Da 5) Notice of Informal Pa 6) Other:	te atent Application (PTO-152)				

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DETAILED ACTION

Claim Rejections - 35 USC § 112

- 1. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 2. Claim 1 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 1 is misdescriptive and rendered the claim indefinite. It is misdescriptive to recite "applying a bias voltage Vcc to the drain terminal of the transistor and applying a bias voltage Vcc to the gate terminal of the transistor so that the source terminal and the gate terminal of the transistor are at 0V". The specification teaches that the gate and source of the control transistor, not the transistor, are at 0V. Furthermore, it is unclear that "a bias voltage" recited in lines 8, 9,15 and 17 are the same.

- 3. The following is a quotation of the first paragraph of 35 U.S.C. 112:
 - The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.
- 4. Claim 1 is rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the enablement requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to enable one skilled in the art to which it pertains, or with which it is most nearly connected, to make and/or use the invention. Claim 1, lines 8-10, and the

specification page 6 recite that the gate and drain of the transistor are applied with Vcc and the source of the transistor is applied with ground voltage. However, the transistor is fully ON when Vcc is applied to its gate. The drain and source of the transistor is shorted together. Therefore, the transistor will be damaged with the potential of its drain and source are applied with different voltage potential.

Claim Rejections - 35 USC § 102

5. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 6. Claim 1 is rejected under 35 U.S.C. 102(b) as being anticipated by Storino et al. (USP 6150869).

Insofar as understood, Storino et al.'s figure 3 discloses a method of operating a siliconon-insulator device, wherein the silicon-on-insulator device includes a transistor (112) and a
control transistor (116) such that the transistor and the control transistor share a common source
region and the drain region of the control transistor is electrically connected to the main body of
the transistor, the operating method comprising the following steps: switching the transistor on
by: applying a bias voltage Vcc (leakage VDD via transistor 110) to the drain terminal of the
transistor and applying a bias voltage Vcc to the gate terminal of the transistor (when CLK is low
or 0V) so that the source terminal and the gate terminal of the control transistor are at 0V,
thereby terminating any electrical connection between the main body of the transistor with the

source terminal of the transistor so that the transistor has a characteristic of floating-body siliconon-insulator device, and switching the transistor off by: applying a bias voltage Vcc (Vdd via 110) to the drain terminal of the transistor so that the gate terminal and the source terminal of the transistor are at 0V (when CLK is high or at Vdd, and A and B are high) and applying a bias voltage Vcc to the gate terminal of the control transistor (CLK is high or at Vdd), thereby forming an electrical connection between the main body of the transistor and the source terminal of the transistor so that the transistor has a characteristic of non-floating body silicon-oninsulator device.

Conclusion

7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. These references are cited as interest because they show some circuits analogous to the claimed invention.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Quan Tra whose telephone number is 571-272-1755. The examiner can normally be reached on 8:00 A.M.-5:00 P.M..

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Timothy Callahan can be reached on 571-272-1740. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Quan Tra

Primary Examiner

February 08, 2005